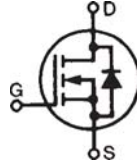


# HiPerFET™ Power MOSFET Q2-Class

## IXFL80N50Q2

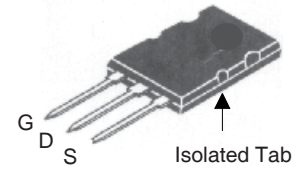
(Electrically Isolated Tab)

N-Channel Enhancement Mode  
Avalanche Rated, Low  $Q_g$ , Low Intrinsic  $R_G$   
High  $dV/dt$ , Low  $t_{rr}$



$$\begin{aligned} V_{DSS} &= 500V \\ I_{D25} &= 55A \\ R_{DS(on)} &\leq 66m\Omega \\ t_{rr} &\leq 250ns \end{aligned}$$

ISOPLUS264™ (IXFL)



G = Gate      D = Drain  
S = Source

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	500	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GS} = 1M\Omega$	500	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	55	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	320	A
$I_A$	$T_C = 25^\circ\text{C}$	80	A
$E_{AS}$	$T_C = 25^\circ\text{C}$	5	J
$dV/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$	20	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	380	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.063 in.) from case for 10s	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic body for 10s	260	$^\circ\text{C}$
$F_C$	Mounting force	30..120/6.7..27	N/lbs
$V_{ISOL}$	50/60 Hz, RMS $t = 1$ min	2500	V~
	$I_{ISOL} \leq 1$ mA $t = 1$ s	3000	V~
<b>Weight</b>		10	g

### Features

- Electrically isolated mounting tab
- Double metal process for low gate resistance
- Unclamped Inductive Switching (UIS) rated
- Low package inductance  
- easy to drive and to protect
- Fast intrinsic diode

### Applications

- DC-DC converters
- Switched-mode and resonant-mode power supplies
- DC choppers
- Pulse generation
- Laser drivers

### Advantages

- 2500 V~ Electrical isolation
- ISOPLUS 264™ package for clip or spring mounting
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0$ V, $I_D = 1$ mA	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8$ mA	3.0		5.5 V
$I_{GSS}$	$V_{GS} = \pm 30$ V, $V_{DS} = 0$ V			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0$ V $T_J = 125^\circ\text{C}$			100 $\mu\text{A}$ 5 mA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 40$ A, Note 1			66 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}, I_D = 40\text{A}$ , Note 1	50	65	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		12.8	nF
$C_{oss}$			1640	pF
$C_{rss}$			440	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 40\text{A}$ $R_G = 1\Omega$ (External)		29	ns
$t_r$			25	ns
$t_{d(off)}$			60	ns
$t_f$			11	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 40\text{A}$		250	nC
$Q_{gs}$			80	nC
$Q_{gd}$			120	nC
$R_{thJC}$			0.33	$^\circ\text{C/W}$
$R_{thCS}$		0.15		$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			80 A
$I_{SM}$	Repetitive, pulse width limited by $T_{JM}$			320 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 25\text{A}, V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$			250 ns
$Q_{RM}$			1.4	$\mu\text{C}$
$I_{RM}$			12	A

Note: 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

**ISOPLUS264™ (IXFL) Outline**

Note: Bottom heatsink meets

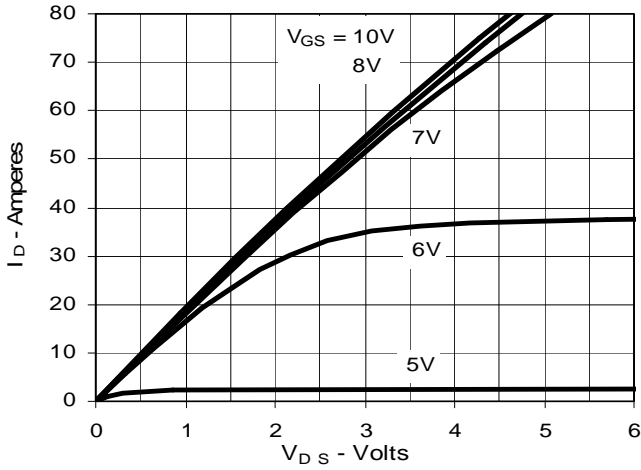
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.102	.118	2.59	3.00
A2	.046	.055	1.17	1.40
b	.045	.055	1.14	1.40
b1	.087	.102	2.21	2.59
b2	.111	.126	2.82	3.20
c	.020	.029	0.51	0.74
D	1.020	1.040	25.91	26.42
E	.770	.788	19.56	20.09
e	.215 BSC		5.46 BSC	
L	.780	.820	19.81	20.83
L1	.080	.102	2.03	2.59
Q	.210	.235	5.33	5.97
Q1	.490	.513	12.45	13.03
R	.150	.180	3.81	4.57
R1	.100	.130	2.54	3.30
S	.668	.690	16.97	17.53
T	.801	.821	20.34	20.85
U	.065	.080	1.65	2.03

Ref: IXYS CO 0128

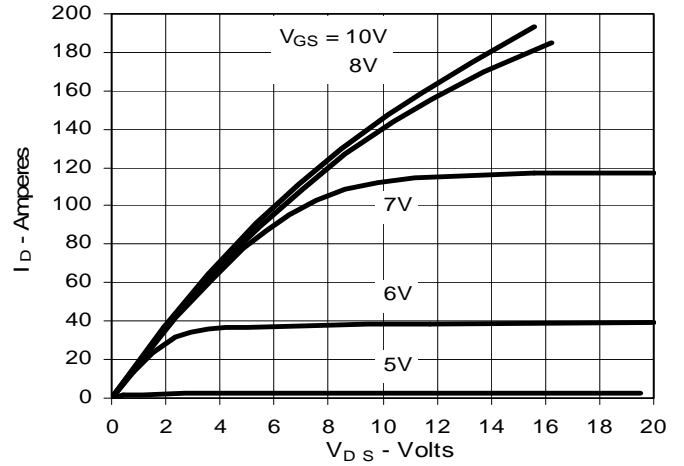
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

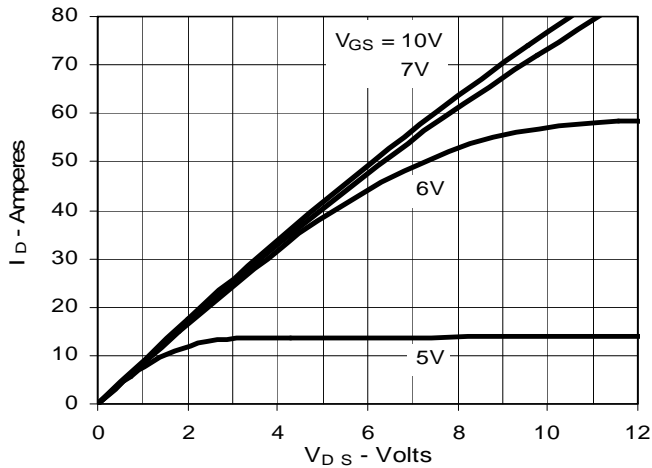
**Fig. 1. Output Characteristics @ 25°C**



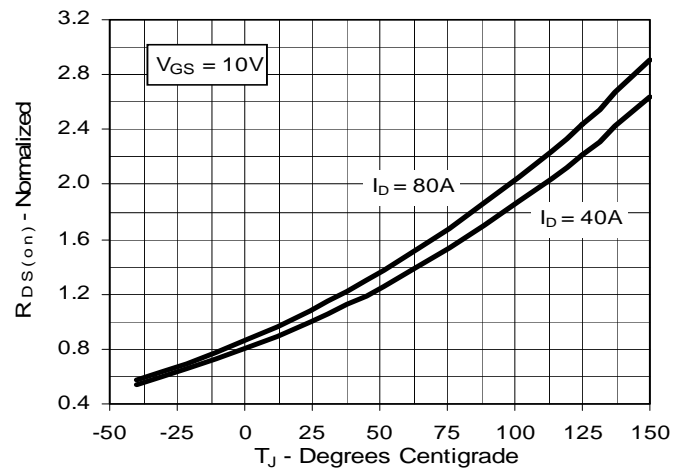
**Fig. 2. Extended Output Characteristics @ 25°C**



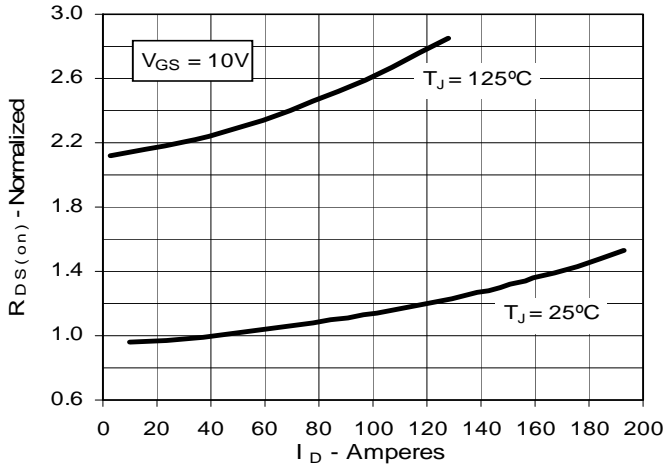
**Fig. 3. Output Characteristics @ 125°C**



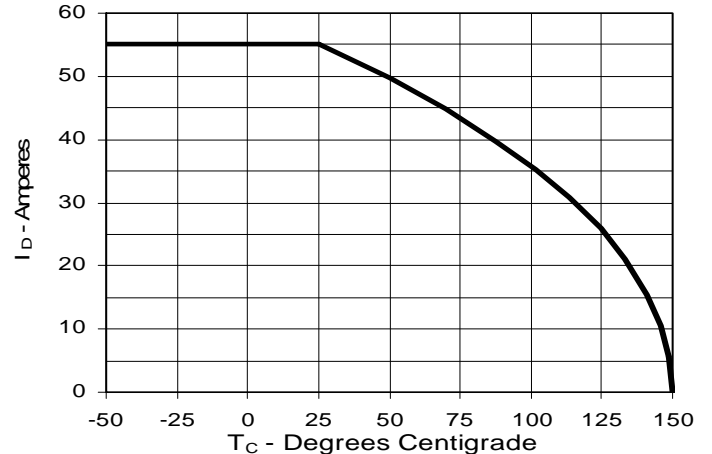
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 40A$  Value vs. Junction Temperature**



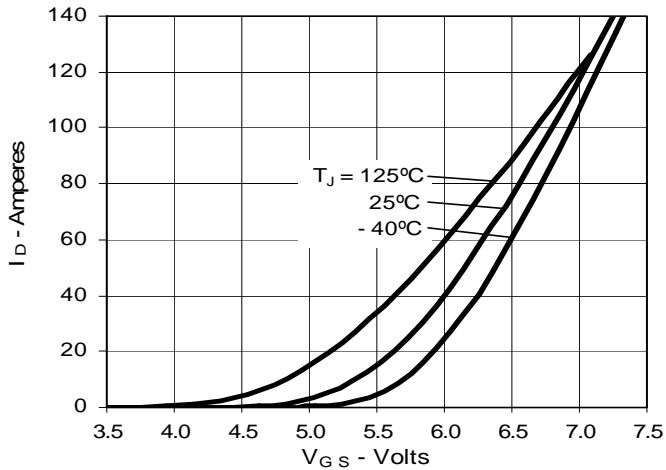
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 40A$  Value vs. Drain Current**



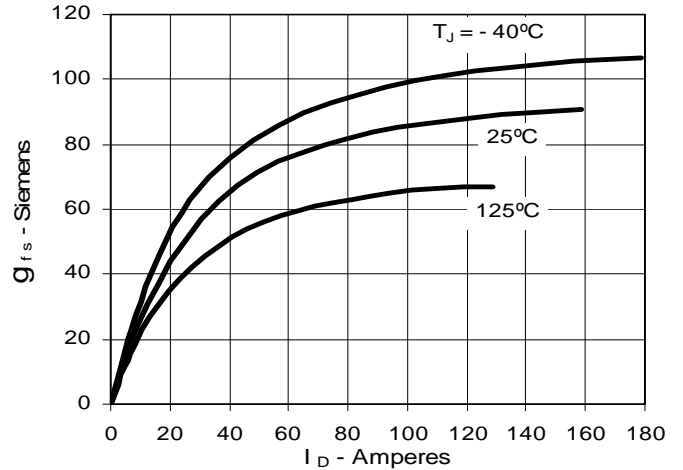
**Fig. 6. Drain Current vs. Case Temperature**



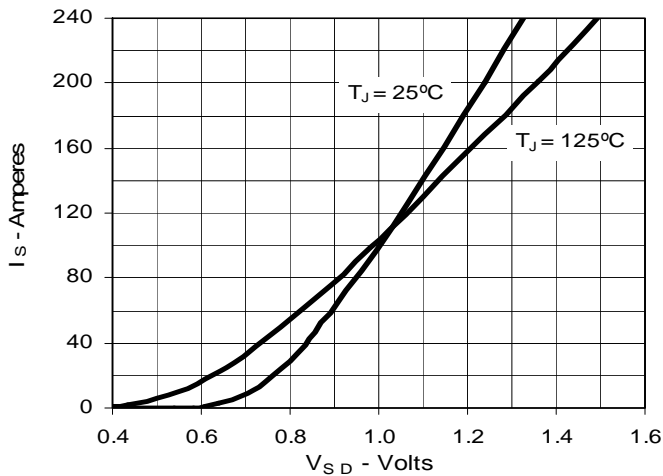
**Fig. 7. Input Admittance**



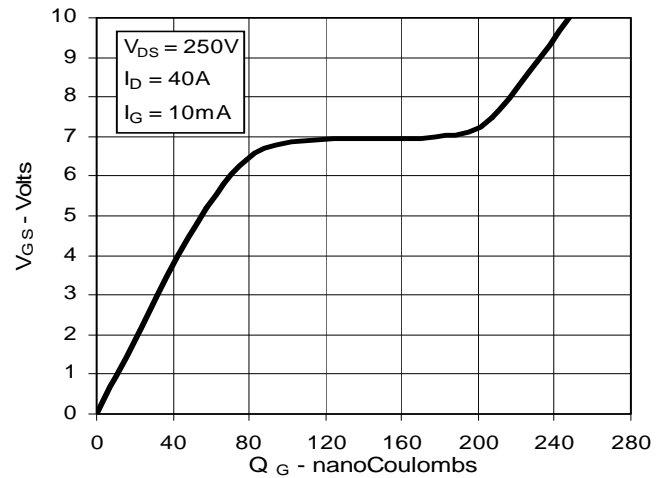
**Fig. 8. Transconductance**



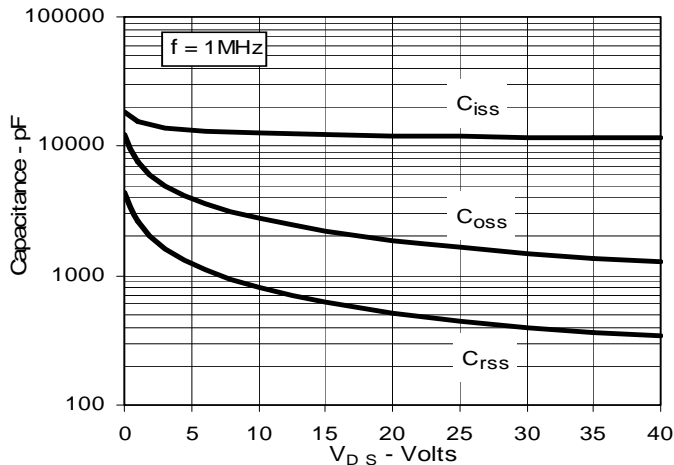
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



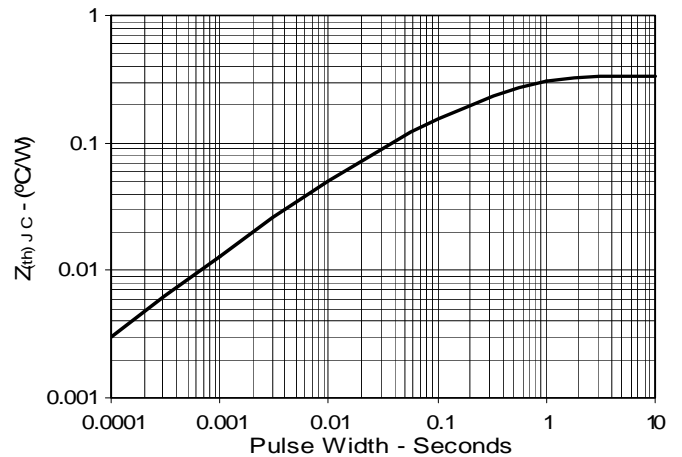
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Impedance**





---

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).